

WHAT IS CLAIMED IS:

1. A stacked photovoltaic device comprising:  
at least one pair of a first photovoltaic  
device and a second photovoltaic device stacked in  
5 order from a light incident side; and  
a selective reflection layer formed between the  
at least one pair of the first photovoltaic device  
and the second photovoltaic device and adapted to  
electrically connect therebetween,  
10 wherein the selective reflection layer has a  
sheet resistance of  $100 \text{ k}\Omega/\square$  or more and  $100 \text{ M}\Omega/\square$  or  
less.
2. The stacked photovoltaic device according to  
15 claim 1, wherein the selective reflection layer has a  
sheet resistance of  $100 \text{ k}\Omega/\square$  or more and  $50 \text{ M}\Omega/\square$  or  
less.
3. The stacked photovoltaic device according to  
20 claim 1, wherein the selective reflection layer has a  
sheet resistance of  $5 \text{ M}\Omega/\square$  or more and  $50 \text{ M}\Omega/\square$  or  
less.
4. The stacked photovoltaic device according to  
25 claim 1, wherein the selective reflection layer has a  
conductivity in a thickness direction of a film which  
is larger than a conductivity in an in-plane

direction of the film.

5. The stacked photovoltaic device according to claim 1, wherein the selective reflection layer  
5 comprises a deposited film formed of metal oxide.

6. The stacked photovoltaic device according to claim 1, wherein the first photovoltaic device has at least a pin-type junction and an i-type layer thereof  
10 comprises amorphous Si:H.

7. The stacked photovoltaic device according to claim 1, wherein the second photovoltaic device has at least a pin-type junction and an i-type layer  
15 thereof comprises Si having crystallinity.

8. The stacked photovoltaic device according to claim 1, wherein the second photovoltaic device has at least a pn-type junction and a p-type  
20 semiconductor and an n-type semiconductor comprise one of monocrystalline Si, polycrystalline Si, and Si having crystallinity.